C30659 Series – 900/1060(E)/1550(E)

Si and InGaAs APD Preamplifier Modules

Excelitas' C30659-1550E InGaAs APD Preamplifier Modules exhibit enhanced damage threshold and greater resilience when exposed to higher optical power densities.

Key Features

- System bandwidths of 50 MHz and 200 MHz
- Ultra-low noise equivalent power (NEP)
- Spectral response range:
  - Si APD: 400 nm to 1100 nm
  - InGaAs APD: 1100 nm to 1700 nm
- Typical power consumption: 150 mW
- ±5 V amplifier operating voltages
- 50 Ω AC load capability (AC-Coupled)
- Hermetically sealed TO-8 package
- High reliability
- Fast overload recovery
- Pin-to-pin compatible with the C30950
- Light entry angle, over 130°
- Model 1550E exhibits enhanced damage threshold
- RoHS-compliant

Applications

- LIDAR
- Range finding
- Laser designation
- Confocal microscopy
- High-speed, extreme low-light detection
- Distributed temperature sensing (DTS)
- Analytical instrumentation
- High-speed, free-space optical communication

Si and InGaAs APD Preamplifier Modules

Table 1. Ordering guide

Model	Nominal Bandwidth	Wavelength Response	Detector Type	Detector Material	Active Diameter	Comments
C30659-900-R8AH	50 MHz	900 nm	C30817EH	Silicon	0.8 mm	
C30659-900-R5BH	200 MHz		C30902EH		0.5 mm	
C30659-1060-3AH	50 MHz	1064 nm (optimized)	C30956EH		3.0 mm	
C30659-1060E-3AH						Enhanced damage
C30659-1060-R8BH	200 MHz		C30954EH		0.8 mm	
C30659-1060E-R8BH						Enhanced damage
C30659-1550-R2AH	50 MHz	1550 nm	C30662EH	InGaAs	0.2 mm	
C30659-1550E-R2AH						Enhanced damage
C30659-1550-R08BH	200 MHz		C30645EH		0.08 mm	
C30659-1550E-R08BH						Enhanced damage

Table 2. Absolute – Maximum Ratings, Limiting Values

Detector type	C30659-900-R8AH (Silicon APD)		C30659-900-R5BH (Silicon APD)		C30659-1060(E) Models (Silicon APD)		C30659-1550(E) Models (InGaAs APD)		
Parameter	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Units**
Photodiode HV bias voltage (Note 1)									
at T_A = +70˚C		600		350		600		100	V
at T_A = -40˚C		300		210		300		50	V
Incident radiant flux, Φ_M, (Note 2)									
average (Note 3)		0.1		0.1		0.1		2	mW
peak (Note 4)		50		50		50			mW
peak (Note 5)							4 (-1550)		kW/cm²
							1000 (-1550E)		kW/cm²
Case temperature									
storage, T_{stg}	-50	100	-50	100	-50	100	-50	100	˚C
operating, T_A	-40	70	-40	70	-40	70	-20	70	˚C
Preamplifier bias voltage	±4.5	±5.5	±4.5	±5.5	±4.5	±5.5	±4.5	±5.5	V

Note 1: The operating voltage (V_{op}) must remain below the breakdown voltage (V_{br}), these values are worst-case estimates. HV voltage current should be limited externally to less than 1 mA.
Note 2: As demonstrated in laboratory conditions.
Note 3: Based on 0.5 W electrical power on the high voltage (HV) supply.
Note 4: Test with 30 ns pulse width.
Note 5: Tested at 1060 nm, 10 ns pulse width and 1 kHz pulse repetition rate
Note 6: Stresses above those listed under above values may cause permanent damage to the device.
Note 7: Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 3. Performance Specifications – C30659-900 Models (900 nm peak response Si APD)

Test conditions: Case temperature = 22˚C, V_{amp} = ±5 V, HV = V_{op} (see Note 1), R_L = 50 Ω AC coupled

Detector Type	C30659-900-R8AH (C30817EH APD)			C30659-900-R5BH (C30902EH APD)			
Parameter	**Min**	**Typical**	**Max**	**Min**	**Typical**	**Max**	**Units**
Active diameter		0.8			0.5		mm
Active area		0.5			0.2		mm²
Nominal field of view α (see Figure 7)		147			148		Degrees
Nominal field of view α' (see Figure 7)		151			151		Degrees
System bandwidth, f_{-3dB}	40	50		175	200		MHz
Bandwidth range		50			200		MHz
Temperature coefficient of V_{op} for constant gain		2.2			0.7		V/˚C
V_{op} for specified responsivity	275	Note 1	435	180	Note 1	260	V
Temperature sensor sensitivity (Note 2)	-1.8	-2.1	-2.4	-1.8	-2.1	-2.4	mV/˚C
Responsivity							
at 830 nm		2700			460		kV/W
at 900 nm		3000			400		kV/W
R_f (Internal feedback resistor)		82			12		kΩ
Noise equivalent power (NEP) (Note 3)							
Average from 100 kHz to f_{-3dB}, Δf = 1.0 Hz							
at 830 nm		14	17		35	55	fW/√Hz
at 900 nm		12	15		40	65	fW/√Hz
Output spectral noise voltage							
Averaged from 100 kHz to f_{-3dB}		35	45		15	25	nV/√Hz
Output impedance	33	40	50	33	40	50	Ω
Rise time, t_r (λ = 830 and 900 nm) 10% to 90% points		7			2		ns
Fall time, t_f (λ = 830 and 900 nm) 90% to 10% points		7			2		ns
Recovery time after overload (Note 4)			150			150	ns
Output voltage swing (1 kΩ load) (Note 5)	2	3		2	3		V_{pp}
Output voltage swing (50 Ω load) (Note 5)	0.7	0.9		0.7	0.9		V_{pp}
DC output offset voltage	-1	0.25	1	-1	0.25	1	V_{DC}
Positive supply current (V_+)		20	35		20	35	mA
Negative supply current (V_-)		10	20		10	20	mA

Note 1: A specific value of V_{op} within the specified range will be supplied with each device.
Note 2: If = 0.1 mA at 25˚C.
Note 3: NEP is calculated as the output spectral noise voltage divided by the typical responsivity.
Note 4: 0 dBm with 250 ns pulses.
Note 5: Pulsed operation, AC-coupled

Table 4. Performance Specifications – C30659-1060 Models (1060 nm optimized response Silicon APD)
Test conditions: Case temperature = 22˚C, Vamp = ±5 V, HV = Vop (see Note 1), RL = 50 Ω AC coupled

Detector type	C30659-1060-3AH C30659-1060E-3AH (C30956EH APD)			C30659-1060-R8BH C30659-1060E-R8BH (C30954EH APD)			
Parameter	**Min**	**Typical**	**Max**	**Min**	**Typical**	**Max**	**Units**
Active diameter		3.0			0.8		mm
Active area		7.1			0.5		mm^2
Nominal field of view α (see Figure 7)		136			149		Degrees
Nominal field of view α' (see Figure 7)		154			153		Degrees
System bandwidth, f_{-3dB}	40	50		175	200		MHz
Bandwidth range		50			200		MHz
Temperature coefficient of V_{op} for constant gain		2.2			2.2		V/˚C
V_{op} for specified responsivity	275	Note 1	425	275	Note 1	425	V
Temperature sensor sensitivity (Note 2)	-1.8	-2.1	-2.4	-1.8	-2.1	-2.4	mV/˚C
Responsivity at 900 nm at 1064 nm R_f (Internal feedback resistor)		 450 280 22			 370 200 12		 kV/W kV/W kΩ
Noise equivalent power (NEP) (Note 3) Average from 100 kHz to f_{-3dB}, Δf = 1.0 Hz at 900 nm at 1064 nm Output spectral noise voltage Averaged from 100 kHz to f_{-3dB}		 55 90 25	 90 125 35		 55 100 20	 80 150 30	 fW/√Hz fW/√Hz nV/√Hz
Output impedance	33	40	50	33	40	50	Ω
Rise time, t_r (λ = 900 and 1064 nm) 10% to 90% points		7			2		ns
Fall time, t_f (λ = 900 and 1064 nm) 90% to 10% points		7			2		ns
Recovery time after overload (Note 4)			150			150	ns
Output voltage swing (1 kΩ load) (Note 5)	2	3		2	3		V_{pp}
Output voltage swing (50 Ω load) (Note 5)	0.7	0.9		0.7	0.9		V_{pp}
DC output offset voltage	-1	0.25	1	-1	0.25	1	V_{DC}
Positive supply current (V_+)		20	35		20	35	mA
Negative supply current (V_-)		10	20		10	20	mA

Note 1: A specific value of V_{op} within the specified range will be supplied with each device.
Note 2: If = 0.1 mA at 25˚C.
Note 3: NEP is calculated as the output spectral noise voltage divided by the typical responsivity.
Note 4: 0 dBm with 250 ns pulses.
Note 5: Pulsed operation, AC-coupled

Table 3. Performance Specifications – C30659-1550/1550E Models (1550 nm peak response InGaAs APD)
Test conditions: Case temperature = 22˚C, V_{amp} = ±5 V, HV = V_{op} (see Note 1), R_L = 50 Ω AC coupled

Detector type	C30659-1550-R2AH C30659-1550E-R2AH (C30662EH APD)			C30659-1550-R08BH C30659-1550E-R08BH (C30645EH APD)			
Parameter	**Min**	**Typical**	**Max**	**Min**	**Typical**	**Max**	**Units**
Active diameter		0.2			0.08		mm
Active area		0.03			0.005		mm²
Nominal field of view α (see Figure 7)		145			145		Degrees
Nominal field of view α' (see Figure 7)		146			146		Degrees
System bandwidth, f_{-3dB}	40	50		175	200		MHz
Bandwidth range		50			200		MHz
Temperature coefficient of V_{op} for constant gain		0.2			0.2		V/˚C
V_{op} for specified responsivity	40	Note 1	70	40	Note 1	70	V
Temperature sensor sensitivity (Note 2)	-1.8	-2.1	-2.4	-1.8	-2.1	-2.4	mV/˚C
Responsivity at 1300 nm at 1550 nm R_f (Internal feedback resistor)		 300 340 68			 80 90 18		 kV/W kV/W kΩ
Noise equivalent power (NEP) (Note 3) Average from 100 kHz to f_{-3dB}, Δf = 1.0 Hz at 1300 nm at 1550 nm Output spectral noise voltage Averaged from 100 kHz to f_{-3dB}		 150 130 45	 180 160 55		 250 220 20	 375 330 30	 fW/√Hz fW/√Hz nV/√Hz
Output impedance	33	40	50	33	40	50	Ω
Rise time, t_r (λ = 1300 and 1550 nm) 10% to 90% points		7			2		ns
Fall time, t_f (λ = 1300 and 1550 nm) 90% to 10% points		7			2		ns
Recovery time after overload (Note 4)			150			150	ns
Output voltage swing (1 kΩ load) (Note 5)	2	3		2	3		V_{pp}
Output voltage swing (50 Ω load) (Note 5)	0.7	0.9		0.7	0.9		V_{pp}
DC output offset voltage	-1	0.25	1	-1	0.25	1	V_{DC}
Positive supply current (V_+)		20	35		20	35	mA
Negative supply current (V_-)		10	20		10	20	mA

Note 1: A specific value of V_{op} within the specified range will be supplied with each device.
Note 2: If = 0.1 mA at 25˚C.
Note 3: NEP is calculated as the output spectral noise voltage divided by the typical responsivity.
Note 4: 0 dBm with 250 ns pulses.
Note 5: Pulsed operation, AC-coupled

Figure 1. Typical Spectral Responsivity

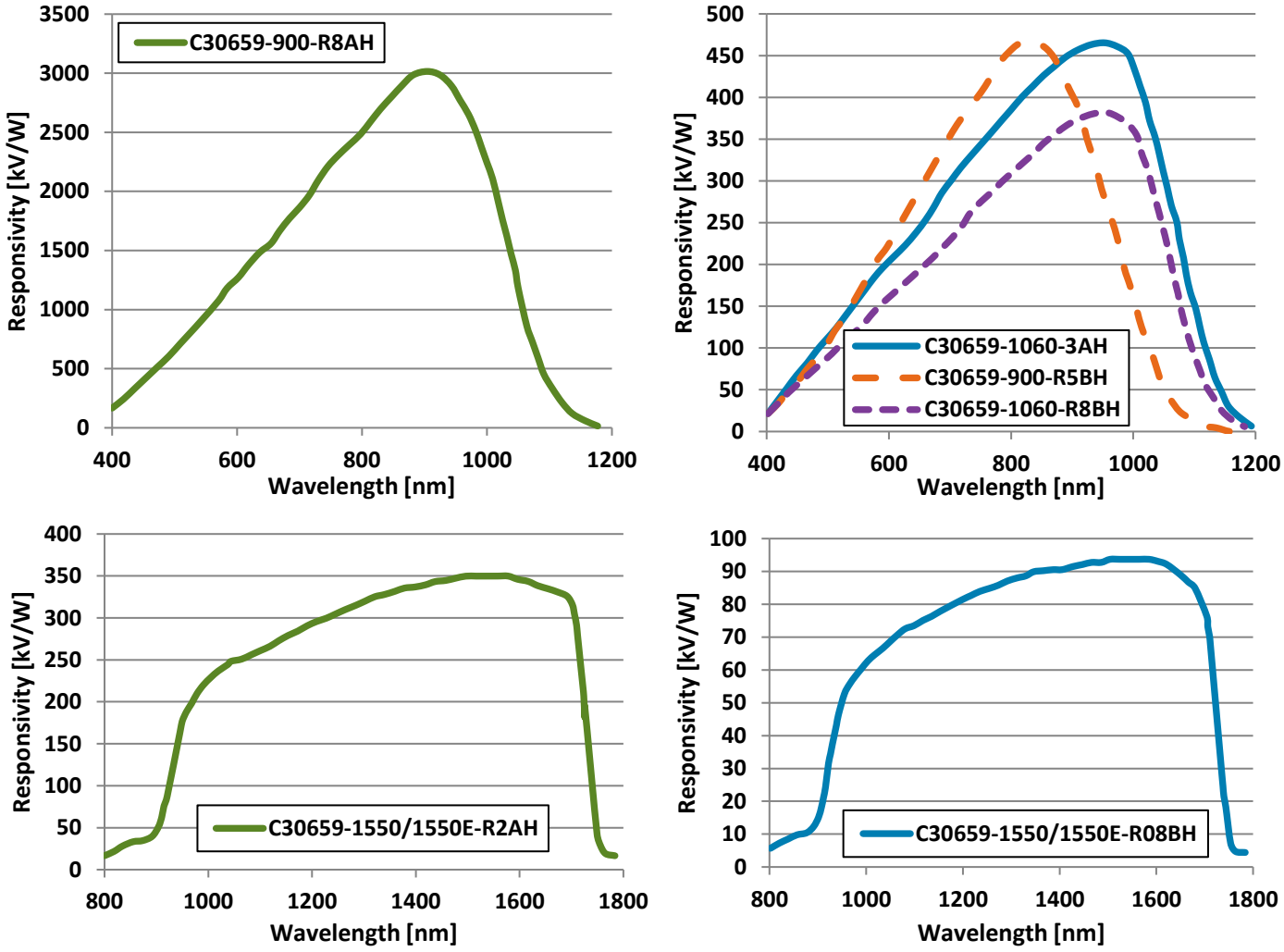


Figure 2. Typical Responsivity as a Function of Operating Voltage – C30659-(900/1060) Series

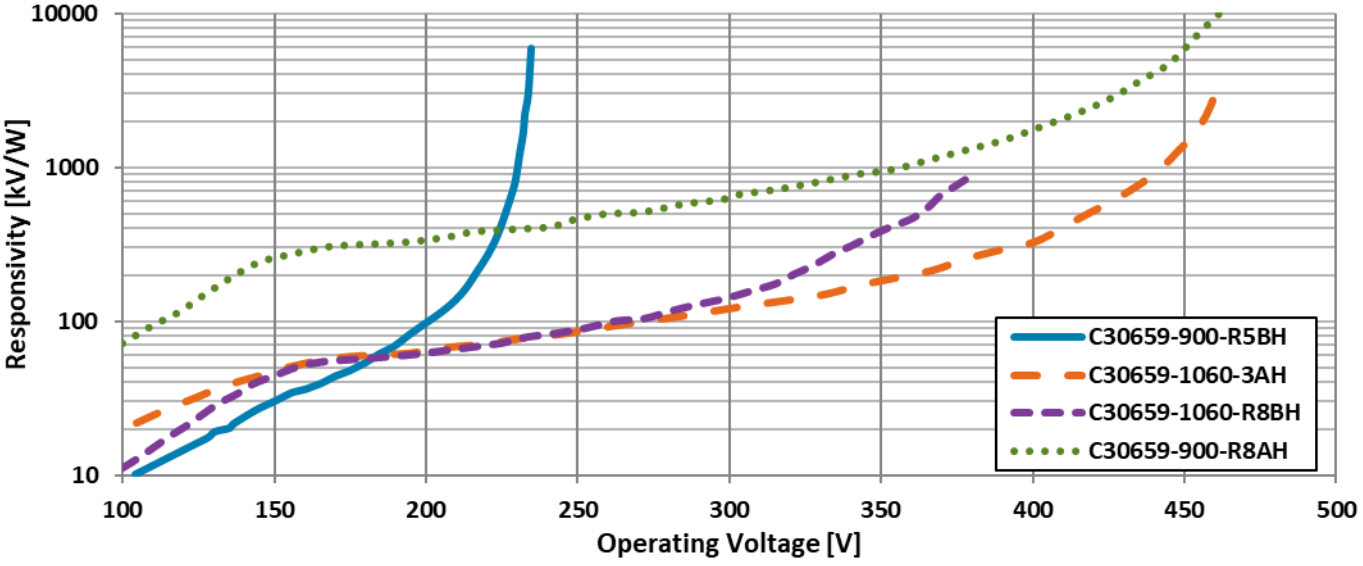


Figure 3. Typical Responsivity as a function of Operating Voltage – C30659-(1550/1550E) Series

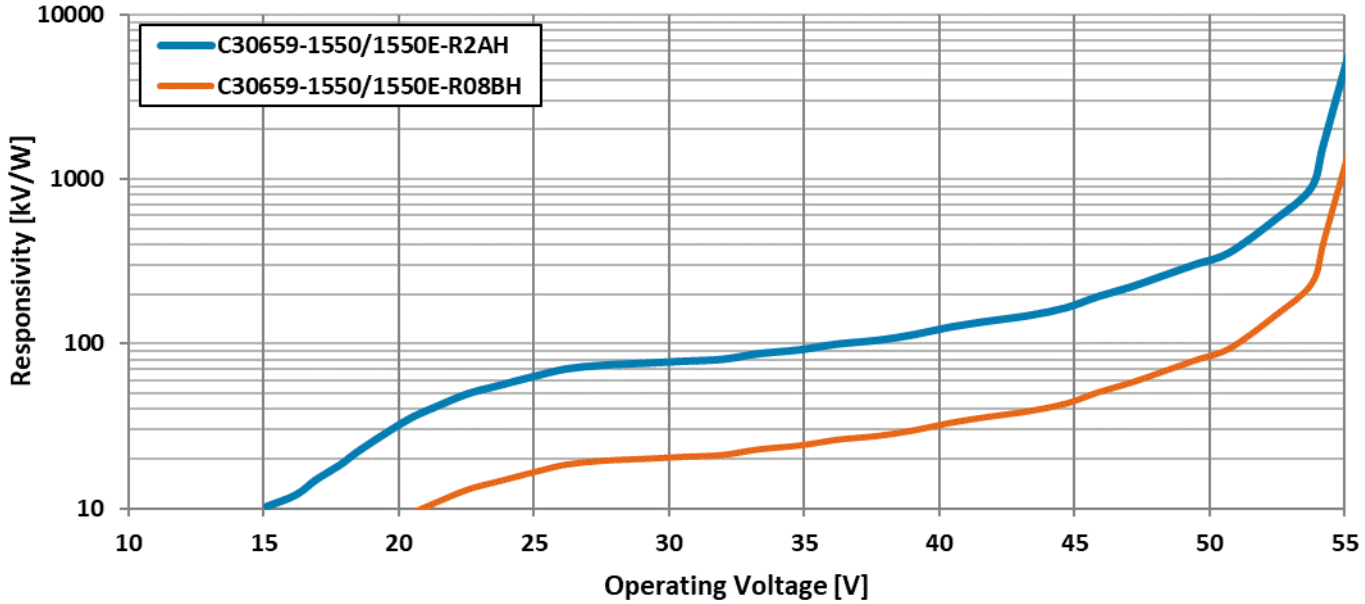
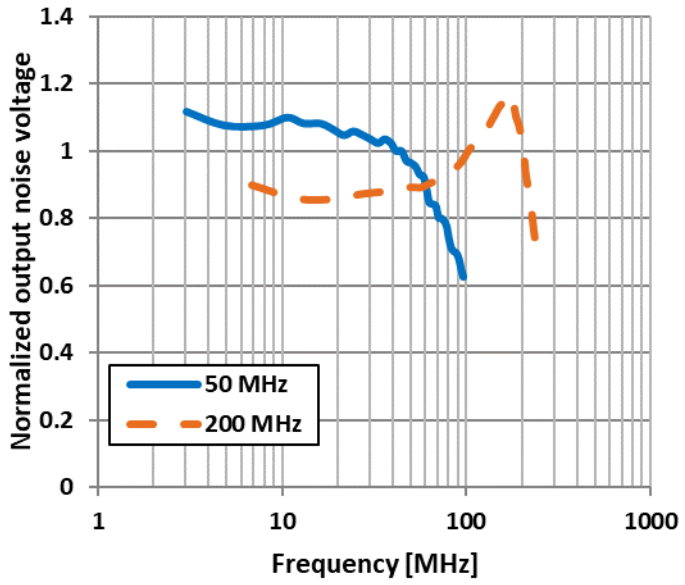
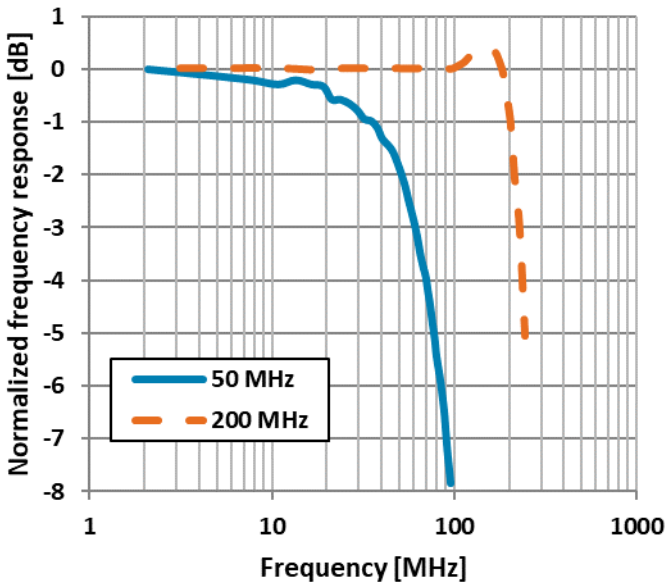


Figure 4. Typical Noise and Frequency response curves





Output voltage noise normalization is calculated using the following formula:

$$V_{n_{normalize}} = \frac{V_n}{V_{n_{average}}}, \text{ where } V_{n_{average}}\left[\frac{V}{\sqrt{Hz}}\right] = \sqrt{\frac{\int_{100kHz}^{f_{-3dB}} V_n^{\,2} \cdot df}{f_{-3dB}}}$$

Figure 5. Typical variation of responsivity as a function of temperature

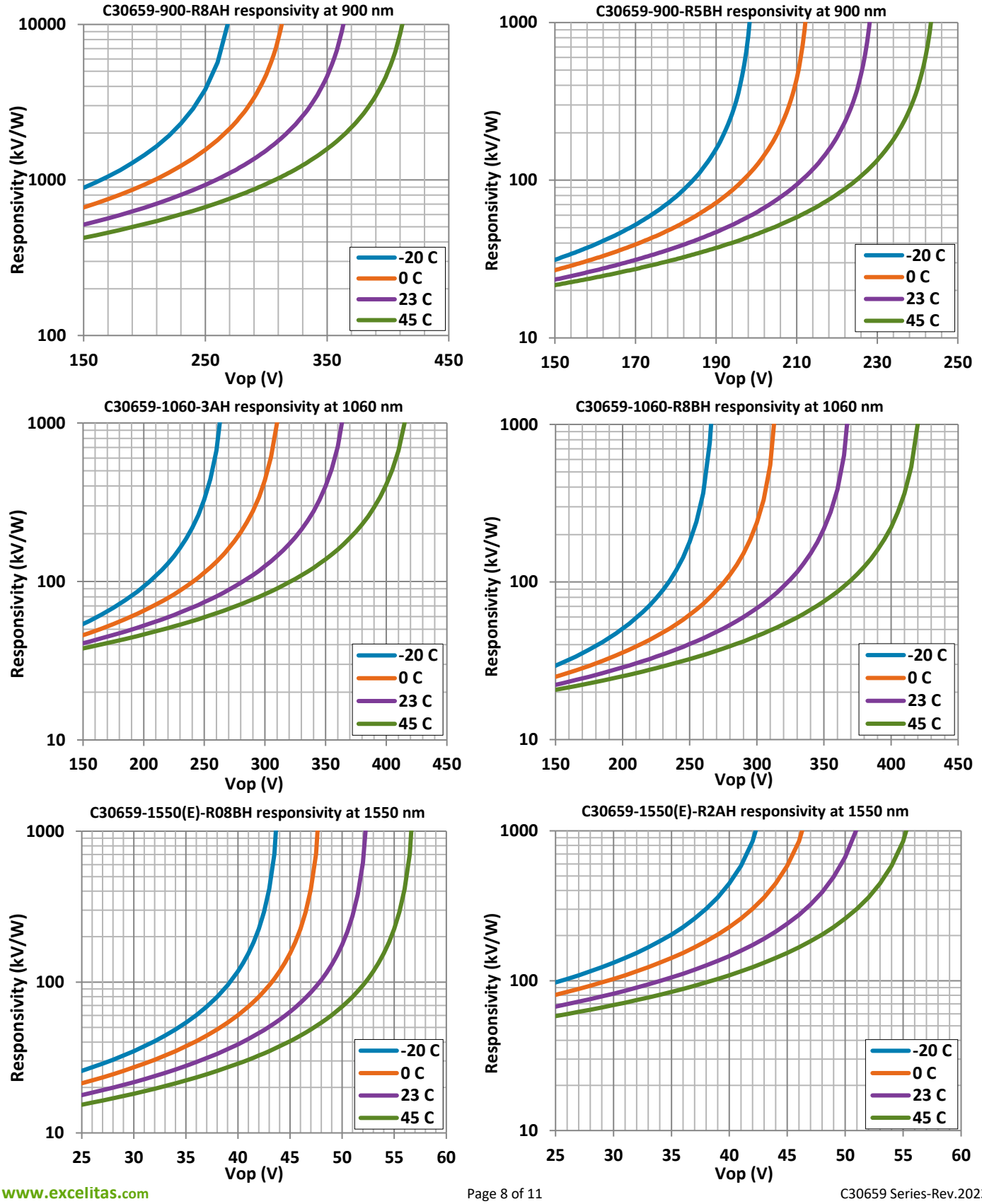
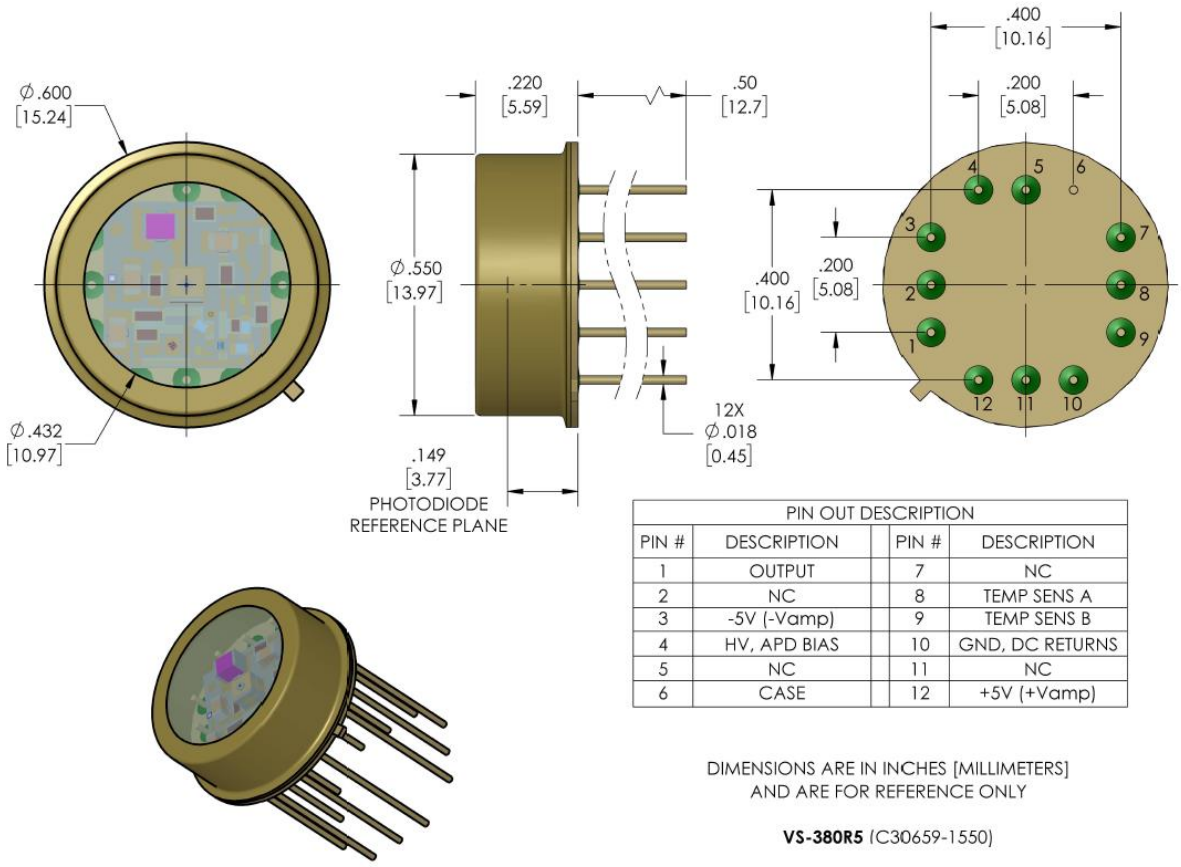


Figure 6. Mechanical Characteristics – C30659 Series



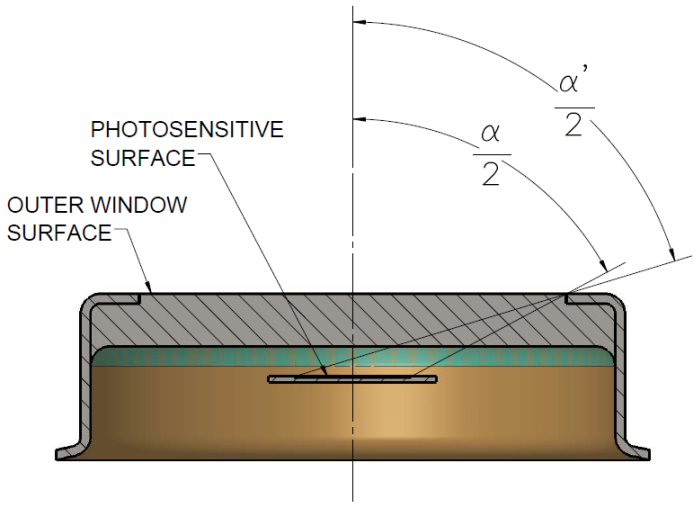
PIN OUT DESCRIPTION			
PIN #	DESCRIPTION	PIN #	DESCRIPTION
1	OUTPUT	7	NC
2	NC	8	TEMP SENS A
3	-5V (-Vamp)	9	TEMP SENS B
4	HV, APD BIAS	10	GND, DC RETURNS
5	NC	11	NC
6	CASE	12	+5V (+Vamp)

DIMENSIONS ARE IN INCHES [MILLIMETERS]
AND ARE FOR REFERENCE ONLY

VS-380R5 (C30659-1550)

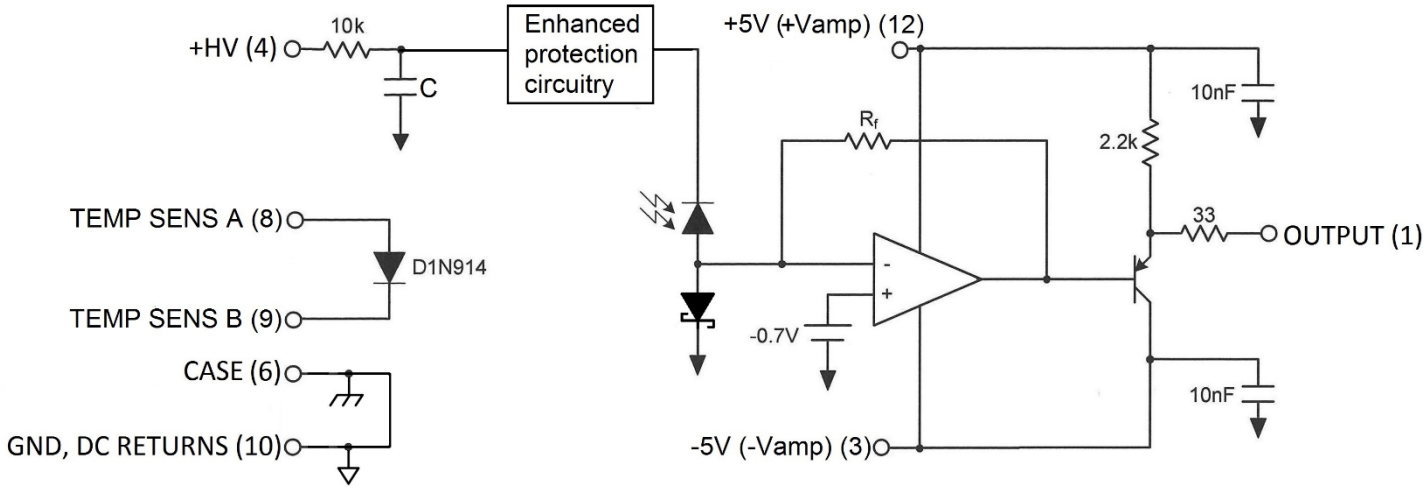
Figure 7. Approximate field of view – C30659 Series

For incident radiation at angles $\leq \alpha/2$, the photosensitive surface is totally illuminated.
For incident radiation at angles $> \alpha/2$, but $\leq \alpha'/2$, the photosensitive surface is partially illuminated.



VS-383

Figure 8. Schematic Block Diagram – C30659 Series



Information

Excelitas Technologies' C30659 Series includes a Si or InGaAs Avalanche Photodiode (APD) with a hybrid preamplifier, in the same hermetically-sealed TO-8 package, to allow for ultra-low noise operation.

The Si APDs used in these devices are the same as used in Excelitas' C30817EH, C30902EH, C30954EH and C30956EH products, while the InGaAs APDs are used in the C30645EH and C30662EH products. These detectors provide very good response between 830 and 1550 nm and very fast rise- and fall-times at all wavelengths. The preamplifier section of the module uses a very low noise GaAs FET front end designed to operate at higher transimpedance than Excelitas' regular C30950 Series.

The C30659 series features an inverting amplifier design with an emitter follower used as an output buffer stage. It remains pin-to-pin compatible with the C30950 Series. To obtain the wideband characteristics, the output of these devices should be capacitively- or AC-coupled to a 50 Ω termination. The module must not be DC-coupled to loads of less than 2 kΩ. For field use, it is recommended that a temperature compensated HV supply be employed to maintain a constant responsivity over temperature.

Excelitas' InGaAs C30659-1060E/1550E Preamplifier Modules are designed to exhibit higher damage thresholds, thus providing greater resilience when exposed to high optical power densities.

Customization of the C30659 Series of APD Preamplifier Modules is available to meet your specific design challenges; modifications include bandwidth and gain optimization, use of different APDs, FC-connectorized packaging.

RoHS Compliance

The C30659 Series of APD Preamplifier Modules are designed and built to be fully compliant with the European Union Directive 2011/65/EU – Restriction of the use of certain Hazardous Substances (RoHS) in Electrical and Electronic equipment.

Warranty

A standard 12-month warranty following shipment applies.

About Excelitas Technologies

Excelitas Technologies is a global technology leader focused on delivering innovative, customized solutions to meet the lighting, detection and other high-performance technology needs of OEM customers.

Excelitas has a long and rich history of serving our OEM customer base with optoelectronic sensors and modules for more than 45 years beginning with PerkinElmer, EG&G, and RCA. The constant throughout has been our innovation and commitment to delivering the highest quality solutions to our customers worldwide.

From aerospace and defense to analytical instrumentation, clinical diagnostics, medical, industrial, and safety and security applications, Excelitas Technologies is committed to enabling our customers' success in their specialty end-markets. Excelitas Technologies has approximately 7,000 employees in North America, Europe and Asia, serving customers across the world.

Excelitas Technologies
22001 Dumberry Road
Vaudreuil-Dorion, Quebec
Canada J7V 8P7
Telephone: (+1) 450.424.3300
Toll-free: (+1) 800.775.6786
Fax: (+1) 450.424.3345

Excelitas Technologies GmbH & Co. KG
Wenzel-Jaksch-Str. 31
D-65199 Wiesbaden
Germany
Telephone: (+49) 611 492 430
Fax: (+49) 611 492 165

Excelitas Technologies Singapore, Pte. Ltd.
8 Tractor Road
Singapore 627969
Telephone: (+65) 6775 2022 (Main number)
Telephone: (+65) 6770 4366 (Customer Service)
Fax: (+65) 6778-1752

Contact us at http://www.excelitas.com/contact

For a complete listing of our global offices, visit www.excelitas.com/locations